

Line 6, after thicker change "for enabling stable mass production and the" to --to enable stable mass production while retaining--;

Line 7, after "device" delete "are still retained";

Line 9, after "with" delete "an".

Page 6

Line 23, before "MOS" change "a" to --an--.

Page 12

Line 9 after "of" change "ths" to --the--.

Page 24

Lines 23, before "of" change "PET" to --FET--.

IN THE CLAIMS:

Please amend Claim 1 as follows:

- sub  
C1
- a.
1. (Amended) A semiconductor device provided at least with source and drain [areas] regions of a first conductive type and [of a high impurity concentration and] a semiconductor layer including a channel [area] region [positioned] between said source and drain [areas] regions, an [insulation] insulating layer covering at least said channel [area] region, and a gate electrode [positioned] arranged close to said [insulation] insulating layer, wherein said channel [area] region [at least] comprises a first channel area of a second conductivity type opposite to the first conductivity type and of low